



First Named Inventor	Leonard Forbes	<b>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b>
Serial No.	10/785,310	
Filing Date	February 24, 2004	
Group Art Unit	2818	
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Confirmation No.	9673	
Attorney Docket No.	400.264US01	
Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES		Sheet 1 of 7

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